

Minji Shon

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RESEARCH INTERESTS

Circuit Reliability, Analog and Mixed-signal IC design, Digital circuit design,
Wafer Level Reliability, Device modeling, Characterization, Evaluation and Analysis

6+ years of strong hands-on experience with DFR (Design For Reliability) as reliability engineer in Quality & Reliability team, Foundry Business, Samsung Electronics

EDUCATION

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|-----------------------|---|---|
| Mar. 2012 – Aug. 2016 | SOGANG UNIVERSITY
<i>B.S., Electronic Engineering</i>
- Graduated with Honors | Seoul, Republic of Korea
GPA(Major) 3.90/4.0, GPA(Total) 3.84/4.0 (1 out of 18, 130 credits) |
| Jan. 2015 – May. 2015 | UNIVERSITY of CONNECTICUT
<i>International Student Exchange Specialization, Electrical and Computer Engineering</i>
- GPA (Major) 4.0/4.0, GPA(Total) 3.77/4.0 (13 credits) | Storrs, CT, USA |

WORK EXPERIENCE

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| Aug. 2016 – Present | SAMSUNG ELECTRONICS
<i>Engineer, Technology Quality & Reliability Group</i> | Republic of Korea |
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Implemented circuit aging environment

- Built up aging PDK components based on accelerated Si test results up to 3nm GAA technology

Improved the coverage and accuracy of transistor's aging models

- Implemented aging models including HCI (Hot Carrier Injection), BTI (Bias Temperature Instability) degradation and TDDB (Time Dependent Dielectric Breakdown) ppm calculation on FinFET Technology
- Improved consistency of Model to Hardware Correlation (MHC) with ring oscillators' frequency degradation
- Provided layout-based self-heat models and simulation environments collaborating with device reliability group
- Implemented statistical aging simulation tools to support process variation based on wafer level Si test results

Provided IP and product-level reliability verification methods

- Guided aging-aware circuit design methods contributing to Samsung's Exynos devices from 14nm to 4nm technology
- Reviewed HCI body-effect and implemented aging models in simulation environments to support 1.8V and 3.3V GPIO by stacking Single Gate devices for 3nm GAA technology
- Collaborated with a Design Technology group to provide guidance of reliability timing margin for Application Processor devices with critical path aging simulation. Put efforts to provide realistic timing margin analyzing BTI effects
- Provided aging-aware verification methods in real operating conditions: Multi-step aging and Power-Down mode simulation methods causing HCI degradation and aging-induced Vt mismatch in ICs
- Implemented verification methods to support memory IPs using overdrive voltage such as eFUSE, OTP and MRAM

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| Oct. 2021 – Dec. 2021 | SAMSUNG ELECTRONICS
<i>Engineer, Dispatch, Design Enablement Team</i> | Republic of Korea |
| <ul style="list-style-type: none">- Dispatched to RF device modeling group to enhance RF device reliability in both DC and AC simulation- Extracted binning and global models for 8nm RF technology | | |

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|--|---|--------------------------|
| Jul. 2016 – Aug. 2016 | SAMSUNG ELECTRONICS
<i>Intern, Technology Quality & Reliability Group</i> | Republic of Korea |
| <ul style="list-style-type: none">- Proposed enhancing dynamic device voltage check methodology by analyzing bias check simulation environment | | |

Jan. 2016 – Jun. 2016

SOGANG UNIVERSITY

Republic of Korea

Undergraduate student research, Signal Processing Systems Laboratory

- Implemented real-time high-speed and high-resolution ultrasound image processing in equipment by using CUDA GPU language (Advisor: Taekyung Song)

HONORS & AWARDS

- Graduated with honors; Dean's List, Sogang University
- Full National Scholarship for Academic Excellence, Korea Student Aid Foundation (KSAF), 2014~2016
- Honors Scholarship for Academic Excellence, Sogang University, 2012~2015

PUBLICATION

- Shim, H., Jo, J., Kim, Y., Jeong, B., **Shon, M.**, Jiang, H., & Pae, S., Aging-aware design verification methods under real product operating conditions. In *2019 IEEE International Reliability Physics Symposium (IRPS)*, pp. 1-4, 2019

ENGINEERING SKILLS & TOOLS

- Development of customized reliability simulation tools from Cadence and Synopsys
- Automation script for aging model implementation

Circuit Netlisting	Finesim; Hspice; Spectre
Reliability Simulation Tools	RelXpert; MOSRA; OMI; Spectre-native
Tool Packages	Cadence Virtuoso; MATLAB
High level-languages	Python; C
Scripting Languages	Perl; TCL

TEACHING EXPERIENCE

SAMSUNG ELECTRONICS

Republic of Korea

Education Mentor

Jan. 2020 – Mar. 2020

- Dispatched as a mentor for SVP(Samsung Value Program) mentoring new employees
- Presented lectures of “Global business manners and etiquettes”; Managed time schedules for education programs
- Performed the role of facilitator providing guidance in team projects to bring out members' creativity and abilities

SAMSUNG ELECTRONICS

Republic of Korea

Education Mentor

Jan. 2022 – Mar. 2022

- Dispatched as a sub-course manager for GNEC(Global New Employee Course)
- Presented lectures of “Communication skills and Creative thinking”

EXTRACURRICULAR ACTIVITIES

SAMSUNG SQUASH CLUB

Republic of Korea

Chief of a Club; Playing Coach

Jan. 2017 – Present

- Held squash competitions and year-end parties; Managed club members and finance; Provided lessons to new members
- Achieved 1st prize in amateur squash competitions held in the Republic of Korea

VOLUNTEER ACTIVITIES

- Participated in the “Wish Angel” program at Samsung; Being a wish angel to sick young children and interacting with them for 6 months and granting their wishes at the end
- Helped science projects during after-school activities in elementary school

LANGUAGE PROFICIENCY

- Proficient in English, Native in Korean
- IBT TOEFL : 102 (Reading: 26, Listening: 29, Speaking: 21, Writing: 26)
- New GRE : 154 (Verbal Reasoning)/ 168 (Quantitative Reasoning)/ 4.0 (Analytical Writing)